Spin-polarized transport through a single-level quantum dot in the K ondo regime

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Nonequilibrium electronic transport through a quantum dot coupled to ferrom agnetic leads (electrodes) is studied theoretically by the nonequilibrium G reen function technique. The system is described by the Anderson model with arbitrary correlation parameter U. Exchange interaction between the dot and ferrom agnetic electrodes is taken into account via an elective molecular eld. The following situations are analyzed numerically: (i) the dot is symmetrically coupled to two ferrom agnetic leads, (ii) one of the two ferrom agnetic leads is half-metallic with almost total spin polarization of electron states at the Fermilevel, and (iii) one of the two electrodes is nonmagnetic whereas the other one is ferrom agnetic. Generally, the Kondo peak in the density of states (DOS) becomes spin-split when the total exchange eld acting on the dot is nonzero. The spin-splitting of the Kondo peak in DOS leads to splitting and suppression of the corresponding zero bias anomaly in the differential conductance.

PACS numbers: $75.20\,\mathrm{H}\,\mathrm{r}$, $72.15\,\mathrm{Q}\,\mathrm{m}$, 72.25.4b, $73.23\,\mathrm{H}\,\mathrm{k}$

I. INTRODUCTION

The Kondo phenomenon in electronic transport through articial quantum dots (QDs) or single molecules attached to nonmagnetic leads was predicted theoretically more than a decade ago [1]. Owing to recent progress in nanotechnology, the phenomenon has been also observed experim entally [2, 3]. Several theoretical techniques have been developed to describe this e ect [4, 5, 6, 7, 8, 9, 10, 11]. The description is usually sim pler in the linear response regime, where equilibrium m ethods can be applied, but it becomes more complex when the system is driven out of equilibrium by an extemal bias voltage [7, 11, 12, 13, 14, 15]. One of the m ethods used to describe non-equilibrium K ondo e ect is the non-equilibrium G reen function technique [5, 16, 17]. To calculate density of states (DOS) and electric current one then needs the retarded/advanced as well as the lesser (correlation) Green functions. These can be derived within some approximation schemes.

It has been shown recently that the K ondo e ect can also occur when replacing nonmagnetic leads by ferromagnetic ones [18, 19, 20, 21, 22], but ferromagnetism of the electrodes generally suppresses the e ect { either partially or totally [19, 22]. However, in some peculiar situations the e ect remains almost unchanged. Suppression of the K ondo anomaly is a consequence of an elective exchange eld due to coupling between the dot and ferromagnetic electrodes. The exchange eld gives rise to spin-splitting of the equilibrium K ondo peak in DOS, and the two components of the splitted peak move away from the Ferm i level, which leads to suppression

of the K ondo anomaly in electrical conductance { similarly as an external magnetic eld suppresses the e ect in nonmagnetic systems. Such a suppression was studied recently by the G reen function technique in the limit of in nite correlation parameter U [19], and was also conmed by numerical renormalization group calculations [23, 24]. However, only QDs symmetrically coupled to two magnetic leads were studied up to now. The K ondo anomaly survives then in the antiparallel magnetic conguration and is signicantly suppressed in the parallel one. Recent experimental observations on C_{60} molecules attached to ferromagnetic (N i) electrodes support these general theoretical predictions [25].

Some features of the non-equilibrium K ondo phenom enon in QDs coupled to ferrom agnetic leads have not been addressed yet. Therefore, in this paper we consider a more general situation. First of all, we consider the case when the two ferrom agnetic electrodes are generally different. In other words, the dot is (spin-)asymm etrically coupled to the ferrom agnetic leads. This leads to qualitatively new results. Second, we consider the case of arbitrary U instead of the limiting situation of in nite U studied in [19]. Third, we introduce an elective exchange eld to describe the dot level renormalization.

We analyze in detail three dierent situations. In the rst case the dot is coupled to two ferrom agnetic leads, and the coupling is fully symmetric in the parallelm agnetic conguration. We show that the equilibrium Kondo peak in DOS is then spin-split in the parallel conguration, whereas no splitting appears in the antiparallelone. The splitting, however, is signicantly reduced for small values of the correlation parameter U. The corresponding zero-bias anomaly in conductance becomes split in the parallel conguration as well [19]. The second situation studied in this paper is the one with asymmetric coupling to two ferrom agnetic leads. As a particular case we consider the situation when one of the ferrom agnetic

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electrodes is half m etallic, with almost total spin polarization of electron states at the Ferm i level. Such structures have been shown recently to have transport characteristics with typical diode-like behavior [26, 27]. Finally, we also analyze the case when one of the electrodes is nonmagnetic whereas the second one is ferromagnetic, and show that one ferromagnetic electrode is su cient to generate spin-splitting of the Kondo anomaly.

The paper is organized as follows. The model and method are brie y described in Sections 2 and 3, respectively. Numerical results for the three dierent situations mentioned above are presented and discussed in Section 4. Summary and general conclusions are given in Section 5.

II. M ODEL

We consider a single-levelQD coupled to ferrom agnetic metallic leads (electrodes) by tunnelling barriers. We restrict our considerations to collinear (parallel and antiparallel) magnetic con gurations and assume that the axis z (spin quantization axis) points in the direction of the net spin of the left electrode (opposite to the corresponding magnetic moment). Antiparallel alignment is obtained by reversing magnetic moment of the right electrode. The whole system is then described by Hamiltonian of the general form

$$H = H_L + H_R + H_D + H_T$$
: (1)

The term s H describe here the left (= L) and right (= R) electrodes in the non-interacting quasi-particle approximation, $H = \begin{bmatrix} & & \\ & & \end{bmatrix}_k & c_k^{\dagger} & c_k & , \text{ where } \end{bmatrix}_k$ the single-electron energy in the electrode for the wavenum berk and spin (=",#), whereas c_k^+ and c_k are the corresponding creation and annihilation operators. The single-particle energy \mathbf{w}_k includes the electrostatic energy due to applied voltage, $\mathbf{n}_k = \mathbf{n}_k^0 + \mathbf{e} \mathbf{u}_e =$, where \mathbf{r}_{k}^{0} is the corresponding energy in the unbiased system, Ue is the electrostatic potential of the -th electrode, e stands for the electron charge (e < 0), is the chemical potential of the -th electrode (the energy is measured from the Fermilevel of unbiased system). Electron spin projection on the global quantization axis is denoted as " for s_z = 1=2 and # and for $s_z = 1=2$. On the other hand, spin projection on the local quantization axis (local spin polarization in the ferrom agnetic material) will be denoted as + for spinm a prity and for spin-m inority electrons, respectively. When local and global quantization axes coincide, then " is equivalent to + and # is equivalent to . (Note, that the local quantization axis in the ferrom agnet is opposite to the local magnetization.)

The term H $_{\text{D}}\,$ in Eq.(1) describes the quantum dot and takes the form

$$X$$
 $H_D = d^+ d + U d_*^+ d_* d_*^+ d_*;$ (2)

where denotes energy of the dot level (spin-dependent in a general case), U denotes the electron correlation param eter, whereas d^{\dagger} and d are the creation and annihilation operators for electrons on the dot. The level energy includes the electrostatic energy due to applied voltage, = $_0$ + eU_e^d , where U_e^d is the electrostatic potential of the dot, and $_0$ is the level energy at zero bias.

The electrostatic potential U_e^d of the dot will be determ ined fully self-consistently from the following capacitance model [28, 29]:

$$X X Y$$
 $e n n_0 = C_L (U_e^d U_e^L) + C_R (U_e^d U_e^R);$
(3)

where n and n_0 are the dot occupation numbers hd^\dagger d i calculated for a given bias and for zero bias, respectively, whereas C_L and C_R denote the capacitances of the left and right tunnel junctions. Self-consistent determination of the dot electrostatic potential makes the description gauge invariant. This is particularly important for strongly asymmetric systems.

The last term , H $_{\rm T}$, in Eq.(1) describes tunnelling processes between the dot and electrodes and is of the form

$$H_{T} = V_{k} c_{k}^{+} d + hx$$
:; (4)

where V_k are the components of the tunnelling matrix, and hx: stands for the Herm itian conjugate term . Ham iltonian (4) includes only spin-conserving tunnelling processes.

III. THEORETICAL FORM ULATION

E lectric current owing from the -th lead to the quantum dot in a nonequilibrium situation is determined by the retarded (advanced) $G^{r(a)}$ and correlation (lesser) G^{c} G reen functions of the dot (calculated in the presence of coupling to the electrodes), and is given by the formula [30]

$$I = \frac{ie}{\pi} \frac{Z}{2} \frac{dE}{2} \quad (E)fG^{<}(E) + f(E)[G^{r}(E) \quad G^{a}(E)]g;$$
(5)

where f (E) is the Ferm i distribution function for the -th electrode. The retarded (advanced) G reen functions can be calculated from the corresponding equation of motion. The key disculty is with calculating the lesser G reen function G $^<$ (E).

In a recent paper [31] we applied the equation of motion method to derive both $G^r(E)$ and $G^<(E)$ G reen functions within the same approximation scheme [32]. However, the approximations for the lesser G reen function $G^<(E)$ do not conserve charge current in asymmetrical systems. Therefore, in the following we assume

constant (independent of energy) coupling param eters, (E) = $2^{-1} V_k V_k$ (E " $_k$) = . As pointed gut in Refs [33, 34], it is then su cient to determ ine (dE = 2) G < (E), while know ledge of the exact form of G (E) is not necessary. Current conservation condition allows then to express the above integral by an integral including retarded and advanced G reen functions only, which in turn allows to rewrite the current formula in the commonly used form,

$$I = \frac{ie}{R} \left[\frac{Z}{R} \right] \left[\frac{dE}{R} \right] \left[\frac{L}{R} \right] \left[\frac{R}{R} \right]$$

Similarly, the occupation numbers, $n = hd^{\dagger} d i$, are then given by the form ula

$$n = i \frac{dE}{2} G^{<}(E)$$

$$= i \frac{dE}{2} \frac{L_{L_{L}}(E) + R_{R_{L}}(E)}{L_{L_{L}}(E) + R_{R_{L}}(E)} [G^{r}(E) G^{a}(E)]; (7)$$

In the following the parameters will be used to param eterize strength of the coupling between the dot and leads. It is convenient to introduce the spin polarization factors p de ned as p = (+)=(+ + where ₊ and are the coupling param eters for spinmajority and spin-minority electrons in the lead, respectively. A coordingly, one may write $_{+} = (1 + p)$ = (1 p), with = (+ +)=2.

The retarded (advanced) G reen function G r(a) of the dot can be calculated only approxim ately, for instance by the equation of motion method. In the approximations introduced by M eir et al [5] one nds

$$G^{r}(E) = \frac{E \quad U(1 \quad n)}{E \quad r(E)](E \quad U) \quad Un \quad r(E)};$$

where r is the corresponding self energy,

$${\rm ^{r}} \; (\!E \;) = \quad {\rm ^{r}}_{0} \; (\!E \;) + \; U \; \frac{(\!E \;) \; n \;\;\; {\rm ^{r}}_{03} \; (\!E \;) \;\;\; L_{0} \;\; {\rm ^{r}}_{03} \; (\!E \;) }{L_{0} \;\; (\!E \;) \;\;\; {\rm ^{r}}_{03} \;\; (\!E \;) };$$

 $w \pm h L_0 = E$ U(1 n), and $\frac{r}{01}$ (E) and $_{03}^{r}$ (E) de ned as

$$_{01}^{r}$$
 (E) = n $_{0}^{r}$ (E) + $_{1}^{r}$ (E); (10)

$$_{03}^{r}$$
 (E) = $_{0}^{r}$ (E) + $_{3}^{r}$ (E): (11)

The self energies $\frac{r}{0}$ (E), $\frac{r}{1}$ (E), and $\frac{r}{3}$ (E) are de-

$$\overset{r}{\underset{0}{\circ}} (E) = \overset{X}{\underset{0}{\circ}} (E) = \overset{X}{\underset{0}{\circ}} (E) = \overset{X}{\underset{E \perp_{iR} \ k}{\times}} \overset{X}{\underset{k}{\circ}} \frac{1}{E \quad "_{k} + i0^{+}}$$

$$= \sum_{E=1.8}^{X} \frac{d^{n}}{2E} = \frac{1}{2} \frac{1}{2}$$
 (12)

$$\begin{array}{c}
 \stackrel{r}{i} (E) = X \quad \stackrel{Z}{=} \frac{d^{"}}{2} A_{i} & \frac{1}{" \quad E} \quad + \quad i \sim =
\end{array}$$

(for = 1,3), where $A_1 = f(")$, $A_3 = 1$, and relaxation time of the intermediate states [5]. This relaxation time is spin dependent and in the low-tem perature lim it is given by the form ula [5]

$$\frac{1}{2} = \frac{1}{2} \times X \times X \quad 0 \quad 0 \quad (\quad 0 \quad + \quad 0)$$

$$\frac{\circ \qquad + \qquad \circ}{(\qquad)(\quad \circ \quad \circ)}; \tag{14}$$

where (x) = 0 for x < 0 and (x) = 1 otherwise. In the lim it of in nite U the G reen function (8) reduces to the well known form,

$$G^{r}(E) = \frac{1 \quad n}{E \quad \frac{r}{0}(E) \quad \frac{r}{1}(E)};$$
 (15)

where $\frac{r}{0}$ (E) is given by Eq.(12) and $\frac{r}{1}$ (E) by

$$_{1}^{r}$$
 (E) = $_{1}^{r}$ (E)

$$X = \frac{Z}{2} = \frac{d''}{2} = \frac{f''}{F + E + + i^{-}};$$
 (16)

de ned by Eq.(14).

The above derived Green functions are su cient to describe qualitatively basic features of the K ondo phenomenon in QDs attached to nonmagnetic leads [5]. However, they are not su cient to describe properly the K ondo phenom enon when the quantum dot is attached to ferrom agnetic leads. The key feature of the system, which is not su ciently taken into account is the splitting of the dot level due to spin dependent tunneling processes [19]. The most natural way would rely on an extension of the G reen function calculations by going beyond the approximations used to derive Eq.(8). This, how ever, leads to cum bersom e expressions. To avoid this, one may treat the problem approximately by introducing 'by hand' the level splitting to the form alism described above. One way to achieve such an objective was proway. Such a renormalization works well in the limit of in nite U . It is however not clear how to extend it to the general case of arbitrary U . Therefore, we decided to include the level splitting via an elective exchange eld. The exchange-induced spin-splitting of the level is particularly in portant for the self-energies $^{\rm r}_1$ (E) and $^{\rm r}_3$ (E), so we replace the bare energy levels in the self-energies $^{\rm r}_1$ (E) and $^{\rm r}_3$ (E) by the corresponding renormalized levels e = g $_{\rm B}$ B $_{\rm ex}$ =2, with the exchange eld calculated from the formula

$$B_{ex} = \frac{1}{g_B} X Re^{\frac{Z}{2}} f''$$

When the bare dot level and spin relaxation time are independent of the spin orientation, $_{"} = _{\#} = _{\#} = _{\#}$ and $_{"} = _{\#} = _{\#} = _{\#}$, the formula (14) acquires the form [35]

$$B_{ex} = \frac{1}{g_B} X Re^{\frac{Z}{2}} f''$$

"
$$\frac{1}{"}$$
 $\frac{1}{i\sim=}$ $\frac{1}{"}$ U $i\sim=$ (18)

To some extent such an approach is similar to that used in Ref.[19], and both approaches give similar results in the limit of large U. This follows from the fact that the expression (17) for exchange eld is basically the expression for the selfenergy $_1^{\rm r}$ (see Eq.(13) for i=1 and E =). However, the approach based on the exchange eld allows to handle easily also the general case of nite U .

IV. NUMERICAL RESULTS

Now, we apply the above described form alism to the K ondo problem in a QD coupled to ferrom agnetic leads. In the num erical calculations described below the energy is measured in the units of D, where D = D = 50 and D is the electron band width. For simplicity, the electron band in the leads is assumed to be independent of the spin orientation and extends from 25D below the Ferm i level (bottom band edge) up to 25D above the Ferm i level (top band edge). The energy integrals will be cut o at E = 25D, i.e., will be limited to the electron band. Thus, the in wence of ferrom agnetic electrodes is included only via the spin asymmetry of the coupling parameters $^{\rm L}$ and $^{\rm R}$. A part from this, in all numerical

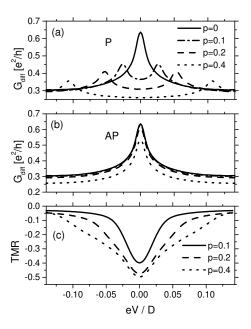


FIG. 1: B ias dependence of the di erential conductance in the parallel (a) and antiparallel (b) con gurations, and the corresponding TMR (c) for indicated four values of the lead polarization $p_L = p_R = p$ (p = 0 corresponds to nonmagnetic leads so the corresponding TMR vanishes and is not shown in part (c)). The parameters assumed for numerical calculations are: kT=D = 0:001, L =D = R =D = 0:1, $_0$ =D = $_0$ =D = $_0$ =D = 0:35, U=D = 500, and ($_0$ 2=C $_L$ 1)=D = ($_0$ 2=C $_R$ 1=D = 0:33.

calculations we assumed kT=D = 0.001 and $_{0"}$ =D = $_{0\#}$ =D = $_{0}$ =D = 0.35.

For positive (negative) bias we assume the electrostatic potential of the left (right) electrode equal to zero. In other words, electrochem ical potential of the drain electrode is assumed to be zero while of the source electrode is shifted up by jeV j. In the following the bias is described by the corresponding electrostatic energy eV. Note that positive eV corresponds to negative bias due to negative electron charge (e < 0).

A. QD coupled to two sim ilar ferrom agnetic leads

Consider rst the situation when both electrodes are made of the same ferrom agnetic metal, and the coupling of the dot to both leads is symmetrical (in the parallel con guration). For numerical calculations we assumed $^{\rm L}_{+}$ =D = $^{\rm R}_{+}$ =D = 0.12 for spin-majority electrons and $^{\rm L}_{-}$ =D = $^{\rm R}_{-}$ =D = 0.08 for spin-minority ones, which corresponds to the spin polarization factor $p_{\rm L}$ = $p_{\rm R}$ = $p_{\rm R}$ =0.2, and $^{\rm L}_{-}$ =D = $^{\rm R}_{-}$ =D = 0.1.

It was shown in Ref.[19] that ferrom agnetism of the electrodes leads to spin splitting of the K ondo peak in the density of states (DOS) in the parallel con guration, whereas no splitting occurs for the antiparallel orientation. Such a behavior of DOS has a signi cant in uence

on the transport properties. First of all, the K ondo peak in DOS leads to zero bias anom aly in the di erential conductance $G_{diff} = @I=@V$. This anomaly is particularly interesting in the parallel con guration, where the spin splitting of the K ondo peak in DOS leads to splitting of the di erential conductance, as shown in Fig.1 (a) for four di erent values of the electrode spin polarization factor p and for large U. For p = 0 there is only a single peak centered at zero bias. W hen the polarization factor becom es nonzero, the peak becom es split into two com ponents located sym m etrically on both sides of the original peak, with the corresponding intensities signicantly suppressed. The splitting of the K ondo anomaly increases with increasing p. Moreover, height of the two components of the K ondo anomaly decreases with increasing p. On the other hand, in the antiparallel con guration there is no splitting of the K ondo peak in the density of states and consequently also no splitting of the K ondo anom aly in the di erential conductance (see Fig.1 (b)). For all polarization values, the anomaly is similar to that in the case of QDs coupled to nonmagnetic leads. However, intensity of the Kondo anomaly decreases with increasing polarization. Di erence between conductance in the antiparallel and parallel con gurations gives rise to the TMR e ect which may be described quantitatively by I^{AP})= I^{AP} , where I^{P} and I^{AP} denote the the ratio (IP current owing through the system in the parallel and antiparallel con gurations at the same bias, respectively. The associated TMR e ect is displayed in Fig.1 (c). One nds negative values of the TMR ratio, which is a consequence of the spin-splitting of the the K ondo peak in the parallel con quration and absence of such a splitting for antiparallel alignment. It is worth to note, that in the absence of the K ondo anomaly the TMR e ect would be positive.

The K ondo anomaly in transport characteristics shown in Fig.1 was calculated for the limit of large U. In Fig.2 we show similar characteristics as in Fig.1, but for dierent values of the correlation parameter U and a constant value of the polarization factor p. The splitting of the K ondo anomaly in the parallel conguration and intensity of the peaks (Fig.2(a)) decrease with decreasing U. In the antiparallel conguration there is no splitting of the K ondo anomaly, but intensity of the K ondo peak decreases with decreasing U. The associated TMR e ect is shown in Fig.2(c). The eect is negative in a certain bias range around the zero bias limit, but absolute magnitude of the eect becomes smaller for smaller values of U. For large bias there is a transition from negative to positive TMR with decreasing U.

B . Q D coupled to one ferrom agnetic and one half-m etallic leads

A ssum e now that one of the electrodes (say the left one) is made of a 3-d ferrom agnetic m etal, the second (right) one is half-m etallic, and the total coupling to the

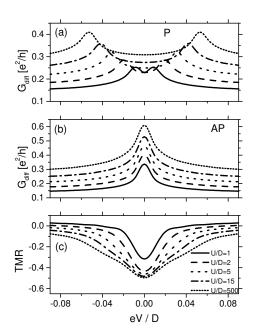


FIG. 2: B ias dependence of di erential conductance in the parallel (a) and antiparallel (b) con gurations, and the corresponding TMR (c) calculated for indicated values of the correlation parameter U and for p=0.2. The other parameters are as in Fig.1.

latter electrode is much smaller than to the form er one. This is rejected in the spin asymmetry of the bare coupling constants, for which we assume $_{+}^{L}$ =D = 0.28 and $_{-}^{L}$ =D = 0.12 for the left electrode, and $_{+}^{R}$ =D = 0.04 and $_{-}^{R}$ =D = 0.002 for the right one. These parameters correspond to p_{L} = 0.4, p_{R} = 0.99, $_{-}^{L}$ =D = 0.2, and $_{-}^{R}$ =D = 0.02. Thus, the spin asymmetry of the coupling to the right electrode is much larger than to the left one. In Fig.3 we show DOS in the parallel (left column) and antiparallel (right column) magnetic congurations, calculated for vanishing as well as for positive and negative bias voltages. Consider now the main features of the spectra in more details, and let us begin with the parallel conguration (left column in Fig.3).

AtV = 0 the K ondo peak in DOS is spin-split, and the intensity of spin-down peak is relatively large, whereas that of the spin-up peak is much smaller. The asym metry in peak intensities is a consequence of the spin asymmetry in the coupling of the dot to m etallic electrodes { this coupling is larger for spin-up electron, which determ ines hight of the K ondo peak for spin-down electrons. When a bias voltage is applied, each of the two K ondo peaks generally becomes additionally split into two components. One of them (the one associated with the coupling to the source electrode) m oves up in energy, whereas position of the second one (the one associated with the drain electrode) remains unchanged. This is because we assumed that the electrochem ical potential of the source electrode shifts up by jeV j, while of the drain electrode is independent of the voltage. For eV > 0 (negative bias), the

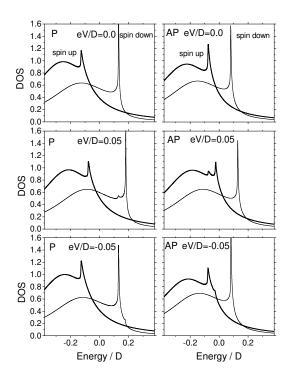


FIG. 3: DOS for spin-up (thick lines) and spin-down (thin lines) electron states on the dot in the parallel (left column) and antiparallel (right column) magnetic con gurations, calculated for three indicated voltages and for $^{\rm L}_{+}$ =D = 0.28, $^{\rm L}_{-}$ D = 0.12, $^{\rm R}_{+}$ =D = 0.04, $^{\rm R}_{-}$ D = 0.0002, U=D = 500, (e²=C_L)=D = (e²=C_R)=D = 10. The other parameters are as in Fig.1.

splitting of the large-intensity (spin-down) peak is clearly visible, although one component of the splitted peak is relatively small. This is just the component associated with the coupling of the dot to the right electrode in the spin-up channel. Since this coupling is relatively small, the corresponding intensity is also small. The second com ponent, in turn, is much larger because it is associated with the coupling to the left electrode in the spin-up channel, which is the dominant coupling in the system considered. Splitting of the low-intensity (spin-up) peak is not resolved. Intensity of the component associated with the coupling to the right electrode in the spin-down channel practically vanishes because this coupling is negligible in the case considered. For eV < 0 (positive bias), the situation is changed. Now the electrochem ical potential of the left electrode is independent of the bias. Consequently, intensity of the components whose position is independent of energy is signi cantly larger than intensity of the other components (the ones associated with the right electrode). As before, the component associated with the coupling to the right electrode in the spin-down channel is not resolved.

Consider now the antiparallel con guration (right column in Fig.3), when magnetic moment of the right electrode is reversed. There is a nonzero spin splitting of the Kondo peak at equilibrium, contrary to the case of

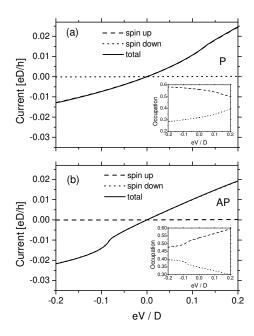


FIG. 4: Current-voltage characteristics in the parallel (a) and antiparallel (b) con gurations, calculated for the param eters as in Fig.3. Current in the spin-down (spin-up) channel in the parallel (antiparallel) con guration almost vanishes so the total current ows in the spin-up (spin-down) channel (the curves presenting the total and spin-up (spin-down) currents are not resolved. The insets show the corresponding occupation numbers. The param eters as in Fig.3

symmetric coupling to the magnetic electrodes, where the spin splitting in the antiparallel con guration vanishes [19]. Apart from this, the situation is qualitatively similar to the one for parallel con guration. The main dierence is that now the bias-induced splitting of the large-intensity peak is not resolved, whereas splitting of the low-intensity peak is resolved.

As in the case of sym metrical coupling described above, the K ondo peaks in DOS give rise to anomalous behavior of the corresponding transport characteristics. Due to the splitting of the equilibrium K ondo peak, the anomaly in DOS does not contribute to transport in the small bias regime. The K ondo peaks enter the 'tunnelling window' at a certain bias, which leads to an enhanced conductance. Such an enhancement is clearly visible in the current-voltage characteristics shown in Fig.4 for both parallel (a) and antiparallel (b) con gurations (solid lines), where for negative values of eV the enhancement is quite signicant, but it is less pronounced for eV > 0. This asymmetry is due to the dierence in intensities of the corresponding K ondo peaks that enter the 'tunnelling window'.

The di erential conductance in the K ondo regime is shown in Fig.5 for parallel (a) and antiparallel (b) magnetic con gurations. In the parallel con guration the K ondo anomaly occurs in the spin-up channel and for eV > 0 only. This may be easily understood by con-

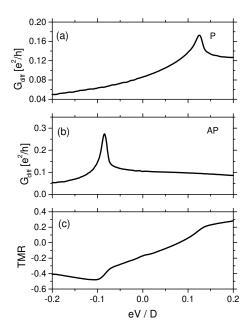


FIG. 5: B ias dependence of the di erential conductance in the parallel (a) and antiparallel (b) con gurations and the corresponding TMR (c), calculated for the same parameters as in Fig.3.

sidering the relevant DOS (see Fig.3, left column). For eV > 0 only the K ondo peak in spin-up DOS can enter the tunnelling window created by the bias. For eV < 0, on the other hand, the K ondo peak in spin-down DOS can enter the tunnelling window. However, the spin down channel is almost non-conducting, so the corresponding peak in the dierential conductance is suppressed. In the antiparallel conguration the K ondo peak in dierential conductance occurs for eV < 0 only. This can be accounted for by taking into account behavior of the K ondo peaks in DOS shown in Fig.3 (right column), and the fact that now the spin-up channel is non-conducting. For eV > 0 only the K ondo peak in the spin-up DOS can enter the tunneling window, whereas for eV < 0 this is the K ondo peak in spin-down DOS (of large intensity).

The corresponding TMR is shown in Fig.5(c). It is interesting to note that TMR is highly asymmetrical with respect to the bias reversal. It becomes positive for eV exceeding a certain positive value, and negative below this voltage. This is a consequence of the fact that for positive eV the K ondo peak in dierential conductance is clearly visible in the parallel conguration (see Fig.5(a)), whereas for eV < 0 the K ondo peak occurs in the antiparallel conguration (see Fig.5(b)). Such a behavior of the conductance and also TMR may be interesting from the point of view of applications in mesoscopic diodes.

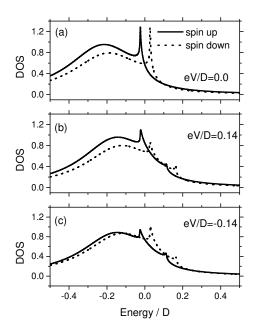


FIG. 6: DOS for spin-up (solid lines) and spin-down (dotted lines) electron states of the dot, calculated for three di erent voltages, and for $^{\rm L}_{\rm +}$ =D = 0:12, $^{\rm L}_{\rm -}$ =D = 0:08, $^{\rm R}_{\rm +}$ =D = $^{\rm R}_{\rm -}$ =D = 0:1, U=D = 500, and (e²=C_L)=D = (e²=C_R)=D = 0:33. The other parameters are as in Fig.1.

C. QD coupled to one ferrom agnetic and one nonm agnetic leads

A specic example of asymmetric systems is the case where one electrode is ferrom agnetic (typical ferrom agnetic 3d m etal) whereas the second one is nonmagnetic. For num erical calculations we assumed $^{L}_{+}$ =D = 0:12, L =D = 0:08 for the left (m agnetic) electrode, and $_{+}^{R}$ =D = $_{-}^{R}$ =D = 0:1 for the right (nonmagnetic) one, which corresponds to p_L = 0.2, p_R = 0, and L =D = R =D = 0:1. As in the other asym m etrical situations studied in this paper, the equilibrium Kondo peak in DOS becom es spin-split. When a bias voltage is applied, each component becomes additionally split, as shown in Fig.6. Variation of the spectra with bias voltage can be accounted for in a similar way as in the case of the dot coupled asymmetrically to two ferromagnetic electrodes. The only dierence is that now all components of the peaks are clearly resolved. This is because all coupling constants are now of comparable magnitude.

The corresponding di erential conductance is shown in Fig.7. Due to the spin splitting of the K ondo peak in DOS, the K ondo anom aly in the conductance becomes split as well, as clearly seen in Fig.7. However, the splitting is asymmetric with respect to the bias reversal. Thus, there is no need to have two ferrom agnetic electrodes to observe splitting of the K ondo anom aly, but it is su cient when only one lead is ferrom agnetic.

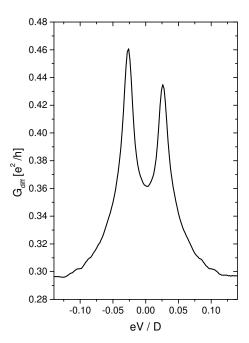


FIG. 7: B ias dependence of the di erential conductance, calculated for the parameters as in Fig.6.

V. SUM MARY AND CONCLUSIONS

In this paper we considered the K ondo problem in quantum dots coupled sym m etrically and asym m etrically to ferrom agnetic leads. As an speci c example of asym — m etrical system s, we considered the case when one electrode is ferrom agnetic, whereas the second one is non-m agnetic.

We showed that ferrom agnetism of the leads gives rise to a splitting of the equilibrium K ondo peak in DOS for all asymmetrical situations. This generally takes place for both magnetic congurations when the two electrodes are dierent. The splitting in both congurations also occurs when both magnetic electrodes are of the same material, but the corresponding coupling strengths to the dot are dierent. Indeed, such a splitting in parallel and also antiparallel congurations was recently observed experimentally [25]. When similar electrodes are symmetrically coupled to the dot, the splitting occurs only in the parallel conguration. An interesting conclusion from the experimental point of view is that the splitting also occurs in the case when one electrode is nonmagnetic.

The spin-splitting of DOS can lead to characteristic splitting of the zero bias anomaly in electrical conductance. This in turn can lead to negative (inverse) tunnelm agnetoresistance e ect. In highly asymmetrical system s TMR can change sign when bias voltage is reversed.

A cknow ledgm ents

The work was supported by the State Comm ittee for Scientic Research through the Research Project PBZ/KBN/044/P03/2001 and $4\,T\,11F\,014\,24$.

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